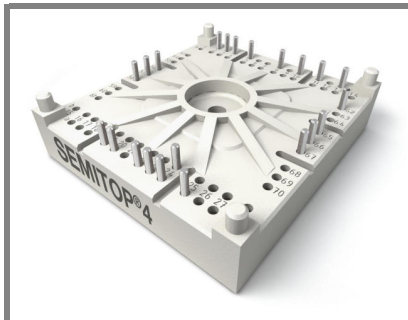


SK75MLI066T



SEMITOP® 4

IGBT Module

SK75MLI066T

Preliminary Data

Features

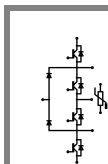
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

- Multi level inverter

Remarks

- $V_{isol} = 3000V$ AC, 1s, 50Hz
- Dynamic measure: DUT= IGBT (Gate pin 55) and Neutral Clamp Diode (Kathode pin 56) as free-wheeling diode

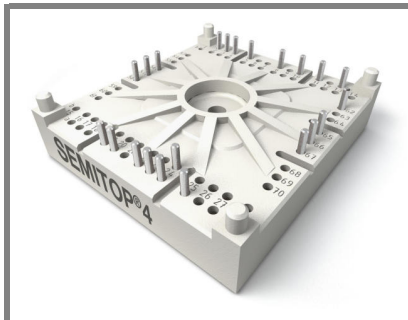


MLI-T

Absolute Maximum Ratings		$T_s = 25^\circ\text{C}$, unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$	600		V
I_C	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	83	A
		$T_s = 70^\circ\text{C}$	67	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	150		A
V_{GES}		± 20		V
t_{psc}	$V_{CC} = 360\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125^\circ\text{C}$ $V_{CES} < 600\text{ V}$	6		μs
Inverse Diode				
I_F	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	92	A
		$T_s = 70^\circ\text{C}$	73	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	150		A
Freewheeling Diode				
I_F	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	92	A
		$T_s = 70^\circ\text{C}$	73	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	150		A
Module				
$I_t(\text{RMS})$				A
T_{vj}		-40 ... +175		$^\circ\text{C}$
T_{stg}		-40 ... +125		$^\circ\text{C}$
V_{isol}	AC, 1 min.	2500		V

Characteristics		$T_s = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1,2\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	$T_j = 25^\circ\text{C}$	0,0038		mA
		$T_j = 125^\circ\text{C}$			mA
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$			600	nA
V_{CE0}		$T_j = 25^\circ\text{C}$	0,8	1,1	V
		$T_j = 150^\circ\text{C}$	0,7	1	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	8	10	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	13	14	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 75\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}_{chiplev.}$	1,45	1,85	V
		$T_j = 150^\circ\text{C}_{chiplev.}$	1,65	2,05	V
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	4,7		nF
C_{oes}			0,3		nF
C_{res}			0,145		nF
Q_G	$V_{GE} = -7V \dots +15V$	650		nC	
R_{Gint}	$T_j = 150^\circ\text{C}$	4		Ω	
$t_{d(on)}$	$R_{Gon} = 4\ \Omega$ $di/dt = 4100\text{ A}/\mu\text{s}$	$V_{CC} = 300V$ $I_C = 75A$	97		ns
t_r			34		ns
E_{on}	$R_{Goff} = 4\ \Omega$ $di/dt = 4100\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$ $V_{GE} = -7/+15V$	1,7		mJ
$t_{d(off)}$			339		ns
t_f			65		ns
E_{off}			2,8		mJ
$R_{th(j-s)}$	per IGBT	0,75		K/W	

SK75MLI066T



SEMITOP® 4

IGBT Module

SK75MLI066T

Preliminary Data

Features

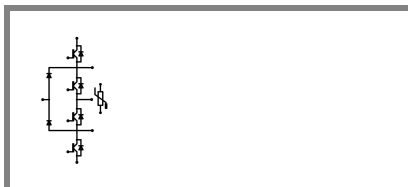
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

- Multi level inverter

Remarks

- $V_{isol} = 3000V$ AC, 1s, 50Hz
- Dynamic measure: DUT= IGBT (Gate pin 55) and Neutral Clamp Diode (Kathode pin 56) as free-wheeling diode

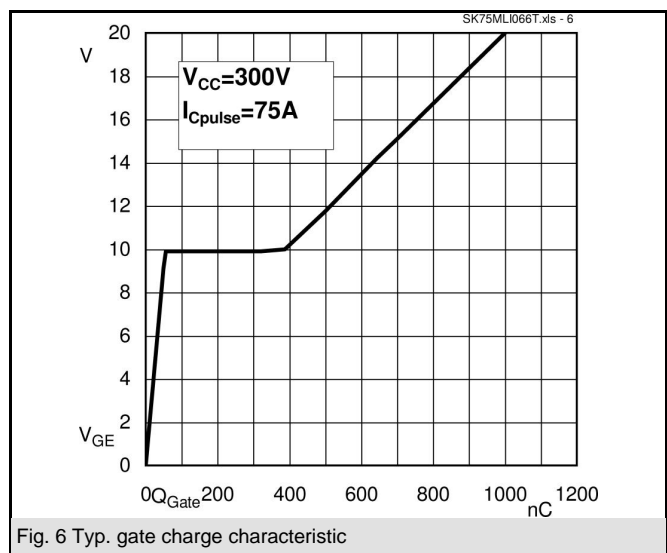
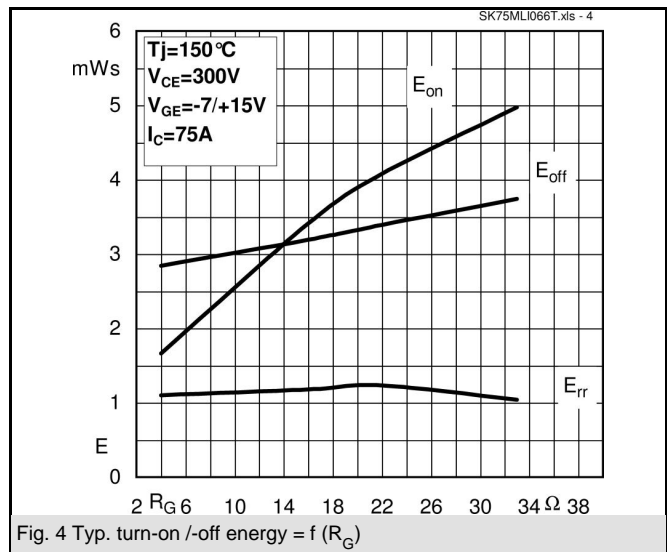
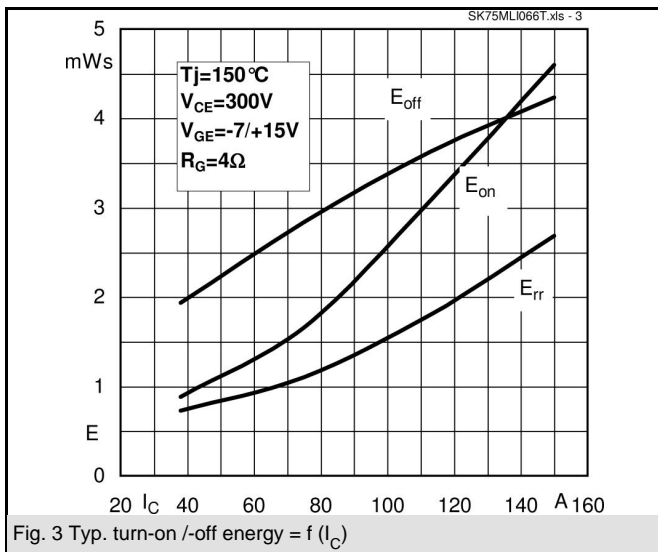
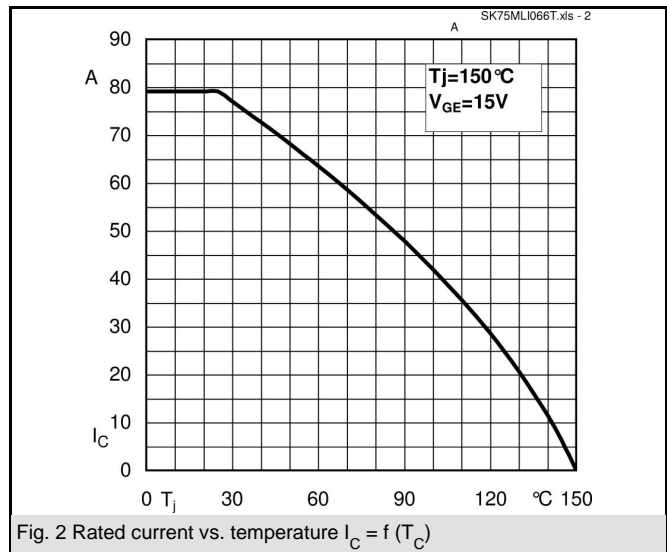
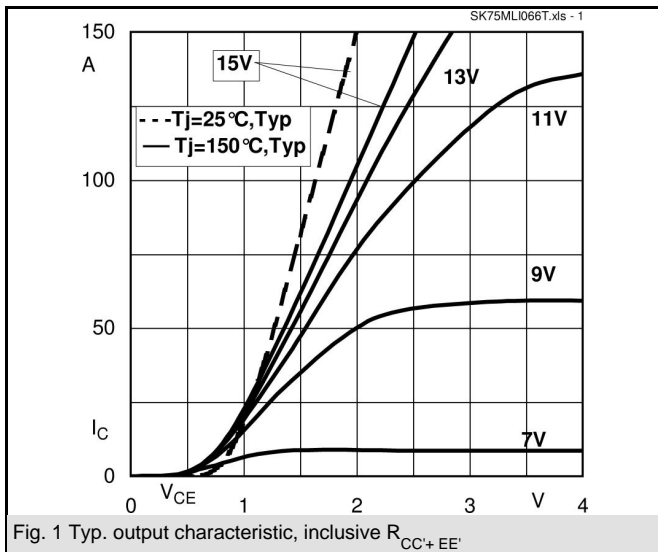


MLI-T

Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 75 A; V_{GE} = 0 V$	$T_j = 25 ^\circ C_{chiplev.}$	1,5	1,7	V
		$T_j = 150 ^\circ C_{chiplev.}$	1,5	1,7	V
V_{F0}		$T_j = 25 ^\circ C$	1	1,1	V
		$T_j = 150 ^\circ C$	0,9	1	V
r_F		$T_j = 25 ^\circ C$	6,7	8	mΩ
		$T_j = 150 ^\circ C$	8	9,3	mΩ
I_{RRM}	$I_F = 75 A$	$T_j = 150 ^\circ C$	65		A
Q_{rr}	$di/dt = 4100 A/\mu s$		4		μC
E_{rr}	$V_R = 300V$		1,1		mJ
$R_{th(j-s)D}$	per diode		1,2		K/W
Freewheeling Diode (Neutral Clamp Diode)					
$V_F = V_{EC}$	$I_{Fnom} = 75 A; V_{GE} = 0 V$	$T_j = 25 ^\circ C_{chiplev.}$	1,5	1,7	V
		$T_j = 150 ^\circ C_{chiplev.}$	1,5	1,7	V
V_{F0}		$T_j = 25 ^\circ C$	1	1,1	V
		$T_j = 150 ^\circ C$	0,9	1	V
r_F		$T_j = 25 ^\circ C$	6,7	8	V
		$T_j = 150 ^\circ C$	8	9,3	V
I_{RRM}	$I_F = 75 A$	$T_j = 150 ^\circ C$	65		A
Q_{rr}	$di/dt = 3100 A/\mu s$		4		μC
E_{rr}	$V_R = 300V$		1,1		mJ
$R_{th(j-s)FD}$	per diode		1,2		K/W
M_s	to heat sink		2,5	2,75	Nm
w			60		g
Temperature sensor					
R_{100}	$T_s = 100^\circ C (R_{25} = 5k\Omega)$		493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



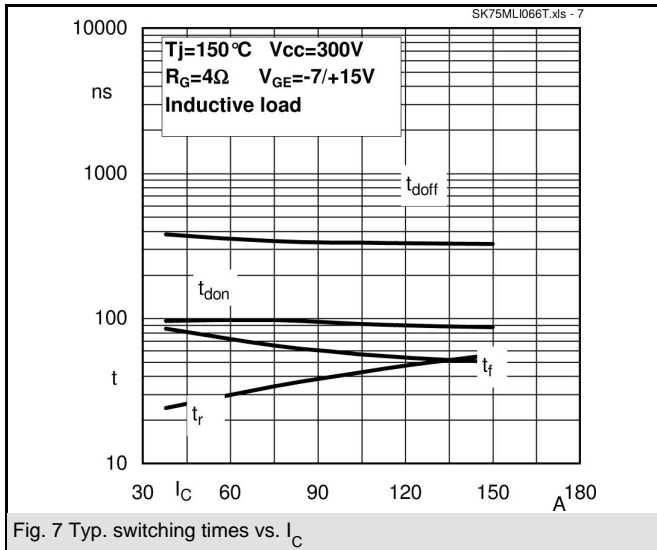


Fig. 7 Typ. switching times vs. I_C

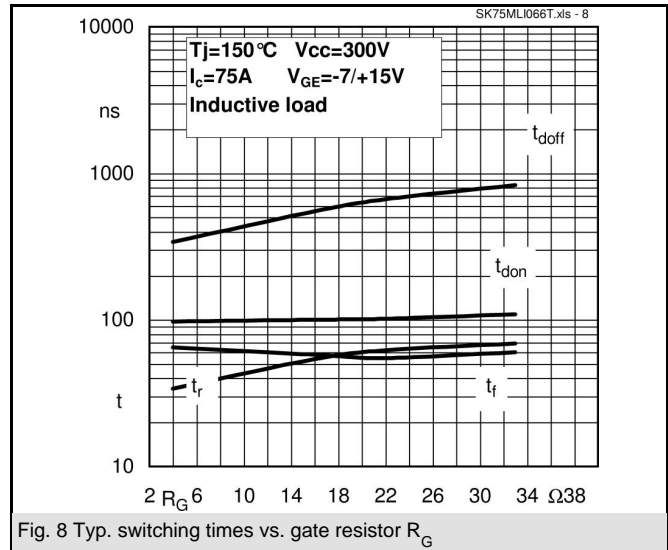


Fig. 8 Typ. switching times vs. gate resistor R_G

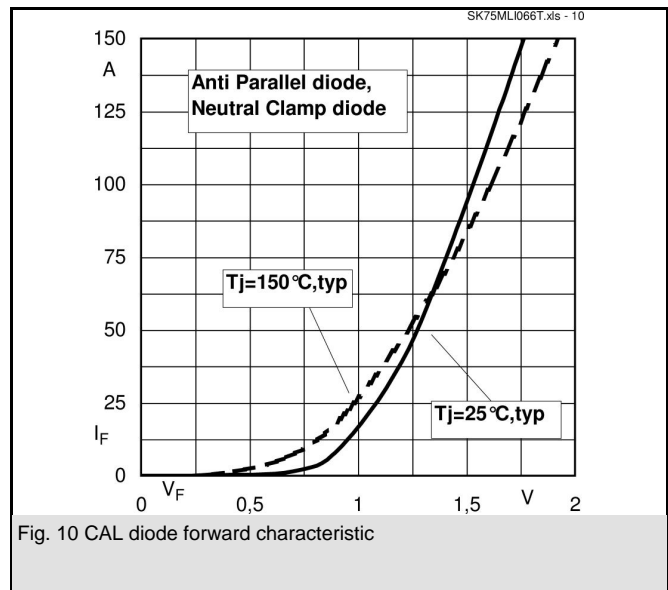
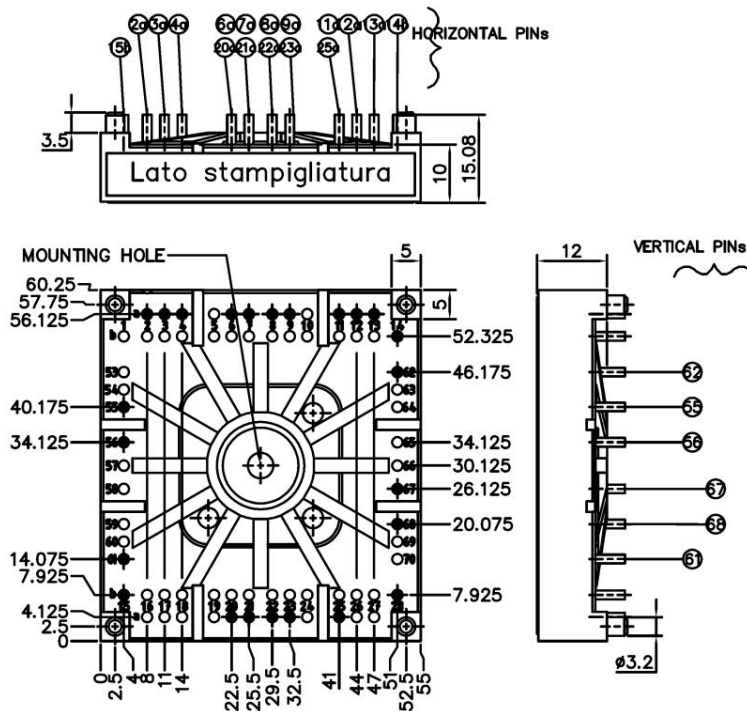


Fig. 10 CAL diode forward characteristic

SK75MLI066T

UL recognized

file no. E 63 532



Case T 88 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)

